

# Fundamentals of Nanoelectronics

ECE495 - Session 6, Sept 4, 2009

## I-V characteristics II

Ref: Chapters 1.3 and 1.4

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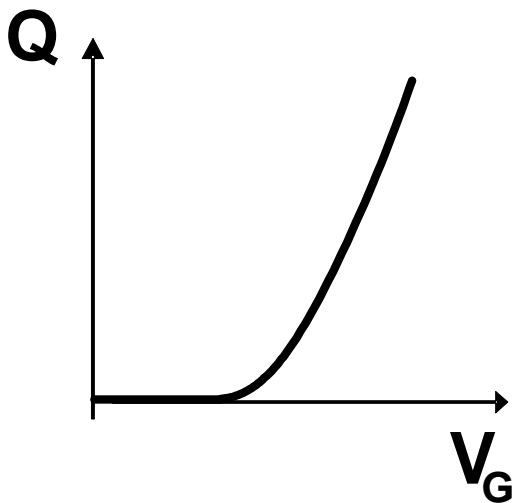
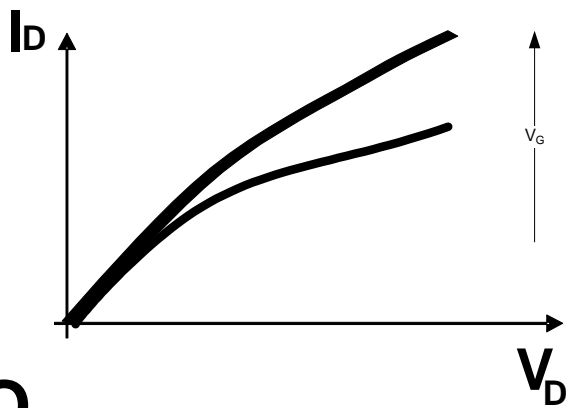
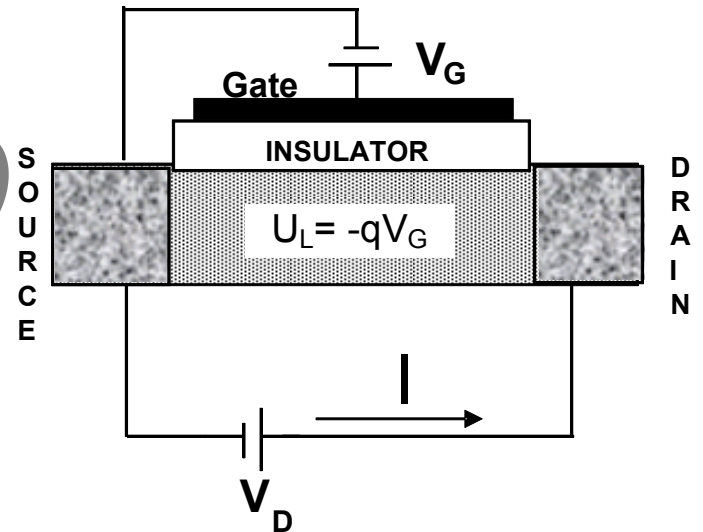
Class notes taken by: Mehdi Salmani

### Review

$$I = \int \frac{q}{\hbar} dE D(E-U) \frac{\gamma}{2} (f_1(E) - f_2(E)) \quad (I)$$

$$N = \int dE D(E-U) \frac{f_1(E) + f_2(E)}{2} \quad (II)$$

$$U = U_L + U_0(N - N_0) \quad (III)$$

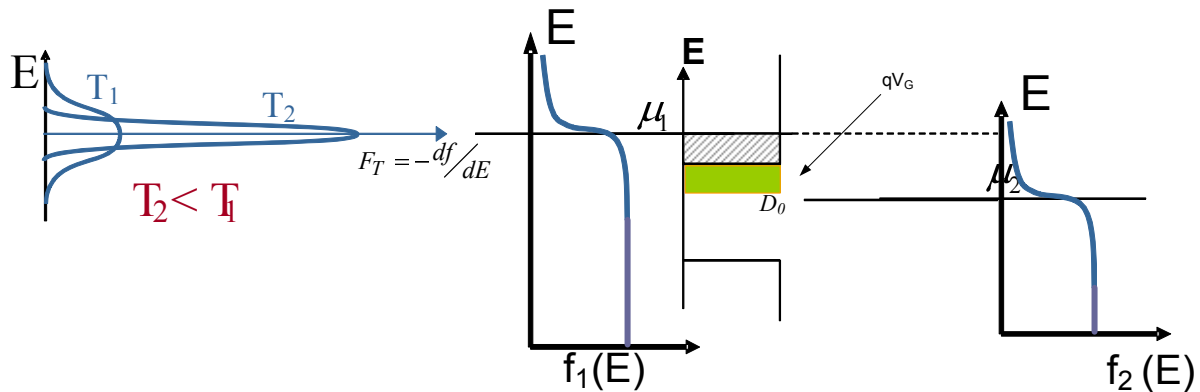


## C<sub>Q</sub> Calculation

$$N = 2 \int dE D(E) f_0(E - U)$$

$$C_Q \Rightarrow -\frac{\partial N}{\partial U} = 2 \int dE D(E) \left(-\frac{\partial f_0}{\partial E}\right) = 2D_0 \quad \& \quad \left(-\frac{\partial f_0}{\partial E}\right) = \delta(E - \mu)$$

$$\frac{\partial(qN)}{\partial(U/q)} = q^2 \frac{\partial N}{\partial U}$$



## Conductance

$$G = \frac{I}{V_D}$$

$$f_0(E) = \frac{1}{1 + e^{\frac{E-\mu}{kT}}}$$

$\frac{I}{V_D} = \frac{2q}{h} \int dE D(E) \frac{\partial f_0}{\partial \mu} (\mu_1 - \mu_2)$  and  $(\mu_1 - \mu_2) = qV_D$  for small potential using Taylor series for  $f_0(\mu_1) - f_0(\mu_2)$  it is correct

$$G = \frac{2q}{h} \int dE D(E) \frac{\partial f_0}{\partial \mu} \quad \text{and} \quad \frac{\partial f_0}{\partial \mu} \equiv -\frac{\partial f_0}{\partial E} \quad \text{this is equivalent with a minus sign}$$

$$\xrightarrow{\text{yields}} G = \frac{2q}{h} \int dE \frac{\gamma}{2} D(E) \left(-\frac{\partial f_0}{\partial E}\right) \quad \text{and} \quad 2\pi\hbar = h \xrightarrow{\text{yields}} G = \frac{2q}{h} \int dE \pi\gamma D(E) \left(-\frac{\partial f_0}{\partial E}\right)$$

In the achieved equation  $\pi\gamma D(E)$  is called number of **Modes**,  $M(E)$ .

For charge calculation  $D(E)$  was enough but for current calculation we need the speed of electrons come in and out.

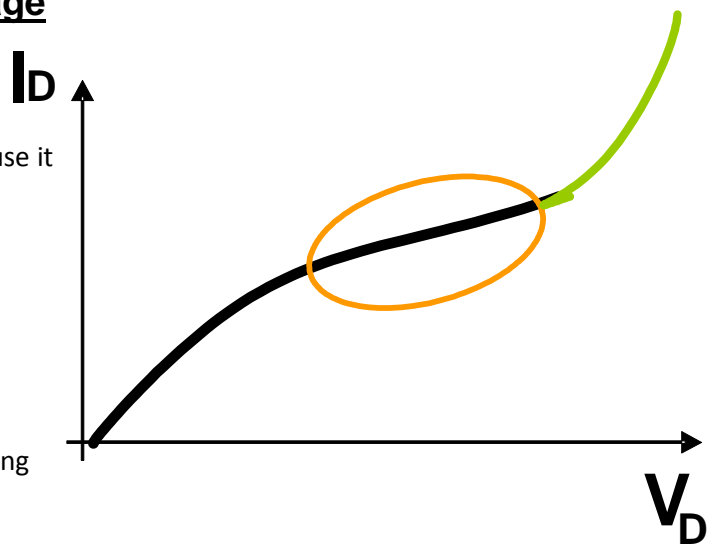
If we know the  $D(E)$  and  $M(E)$  then we could easily calculate I-V.

### Current equation for higher voltage

In I-V graph, in circled part, if we have enough voltage the  $f_2(E) \approx 0$  then we can drop  $f_2$  from current equation. We can assume  $f_2(E) \approx 0$  because it is very lower than where DOS is greater than 0.

$$I = \int \frac{q}{\hbar} dE D(E - U) \frac{\gamma}{2} f_1(E)$$

In this part also current is not fixed due to lowering the  $D(E)$ .



When we put a voltage, then half will be on source side and the other half will be on drain. And DOS is assumed fixed.

$$N \propto f_1/2 \rightarrow N_0/2$$

